

AMENDMENTS TO THE CLAIMS

Please amend the claims as follows.

1. (Currently Amended) A method for manufacturing a nitride semiconductor chip, said method comprising the steps of:

growing nitride crystals of a hexagonal system on a ~~substrate~~-surface of a substrate; and
cutting said substrate along two directions that form a 120 degree angle;
forming a light-emitting section on a central section of the nitride semiconductor chip;
and
forming an electrode at opposing ends of a planar surface of the nitride semiconductor
chip.
2. (Currently Amended) A method according to claim 1, further comprising, between said growing step and said cutting step, the step of grinding a the back surface of said substrate.
3. (Currently Amended) A method according to claim 2, further comprising the step of:

making scratches on one of a the front surface and a [[or]]back surface of said substrate,
between said grinding step and said cutting step, wherein
said cutting step is performed by cutting said substrate along [[the]]directions of said
scratches.
4. (Currently Amended) A method according to claim 1, wherein said semiconductor chip has a planer-planar shape of a rhombus.
5. (Original) A method according to claim 1, wherein said substrate is sapphire.
6. (Original) A method according to claim 1, wherein said nitride crystals include GaN.

7. (Withdrawn) A nitride semiconductor chip, comprising:
 - a substrate; and
 - nitride crystals of a hexagonal system and formed on said substrate; wherein
 - the planer shape of said semiconductor chip is a rhombus having an interior angle of 120 degrees.
8. (Withdrawn) A semiconductor chip according to claim 7, further comprising:
 - a light emitting section formed on the central section of said rhombus of the planer shape of said semiconductor chip; and
 - electrode sections formed at both ends of said rhombus to pinch said light emitting section.
9. (Withdrawn) A semiconductor chip according to claim 8, wherein the planer shape of said electrode sections is triangular.
10. (Withdrawn) A semiconductor chip according to claim 7, wherein said substrate is a sapphire.
11. (Withdrawn) A semiconductor chip according to claim 7, wherein said nitride crystals include a GaN.
12. (New) A method for manufacturing a nitride semiconductor chip, said method comprising the steps of:
 - growing nitride crystals of a hexagonal system on a surface of a substrate;
 - grinding a back surface of said substrate; and
 - cutting said substrate along two directions that form a 120 degree angle.
13. (New) A method according to claim 12, further comprising the step of:
 - making scratches on one of a front and a back surface of said substrate, between said grinding step and said cutting step, wherein
 - said cutting step is performed by cutting said substrate along directions of said scratches.

14. (New) A method according to claim 12, wherein said semiconductor chip has a planar shape of a rhombus.
15. (New) A method according to claim 12, wherein said substrate is sapphire.
16. (New) A method according to claim 12, wherein said nitride crystals include GaN.